



Corrigendum

Corrigendum to “Sensitivity of P-Channel MOSFET to X- and Gamma-Ray Irradiation”

Milić Pejović ¹, **Olivera Ciraj-Bjelac** ², **Milojko Kovačević**,² **Zoran Rajović**,³
and **Gvozden Ilić**³

¹Faculty of Electronic Engineering, University of Niš, Aleksandra Medvedeva 14, 18000 Niš, Serbia

²Vinča Institute of Nuclear Sciences, University of Belgrade, P.O. Box 522, 11001 Belgrade, Serbia

³Electric Power Industry of Serbia, 11000 Belgrade, Serbia

Correspondence should be addressed to Milić Pejović; milic.pejovic@elfak.ni.ac.rs

Received 16 April 2020; Accepted 22 June 2020; Published 31 August 2020

Copyright © 2020 Milić Pejović et al. This is an open access article distributed under the Creative Commons Attribution License, which permits unrestricted use, distribution, and reproduction in any medium, provided the original work is properly cited.

In the article titled “Sensitivity of P-Channel MOSFET to X- and Gamma-Ray Irradiation” [1], there was an error in the drawing of Figure 2, which should be corrected as follows:

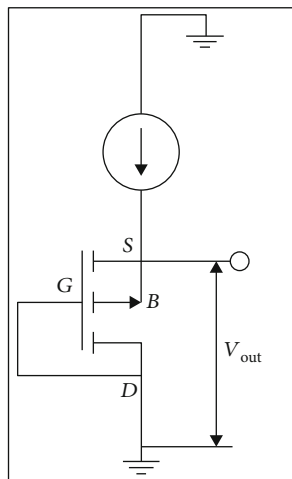


FIGURE 2: Electronic scheme for reader circuit measurement.

References

- [1] M. Pejović, O. Ciraj-Bjelac, M. Kovačević, Z. Rajović, and G. Ilić, "Sensitivity of p-channel MOSFET to X- and gamma-ray irradiation," *International Journal of Photoenergy*, vol. 2013, Article ID 158403, 6 pages, 2013.